

COMPLEMENTARY SILICON POWER TRANSISTORS

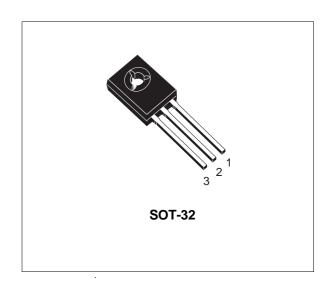
- STMicroelectronics PREFERRED SALESTYPE
- COMPLEMENTARY PNP NPN DEVICES

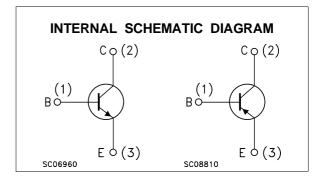
DESCRIPTION

The BD433, BD435, and BD437 are silicon epitaxial-base NPN power transistors in Jedec SOT-32 plastic package, intented for use in medium power linear and switching applications.

The BD433 is especially suitable for use in car-radio output stages.

The complementary PNP types are BD434, BD436, and BD438 respectively.





ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | | | Unit | | |
|------------------|---|-----|------------|-------|-------|----|
| | | NPN | BD433 | BD435 | BD437 | |
| | | PNP | BD434 | BD436 | BD438 | |
| V _{CBO} | Collector-Base Voltage (I _E = 0) | | 22 | 32 | 45 | V |
| Vces | Collector-Emitter Voltage (V _{BE} = 0) | | 22 | 32 | 45 | V |
| V _{CEO} | Collector-Emitter Voltage (I _B = 0) | | 22 | 32 | 45 | V |
| V _{EBO} | Emitter-Base Voltage (I _C = 0) | | | 5 | | V |
| Ic | Collector Current | | | 4 | | Α |
| I _{CM} | Collector Peak Current (t ≤ 10 ms) | | | 7 | | Α |
| Ι _Β | Base Current | | | 1 | | Α |
| P _{tot} | Total Dissipation at T _c ≤ 25 °C | | 36 | | | W |
| T _{stg} | Storage Temperature | | -65 to 150 | | | °C |
| Tj | Max. Operating Junction Temperature | | 150 | | | °C |

For PNP types voltage and current values are negative.

February 2003

BD433 BD434 BD435 BD436 BD437 BD438

THERMAL DATA

| R _{thj-case} | Thermal Resistance Junction-case | Max | 3.5 | °C/W | |
|-----------------------|-------------------------------------|-----|-----|------|--|
| $R_{thj-amb}$ | Thermal Resistance Junction-ambient | Max | 100 | °C/W | |

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

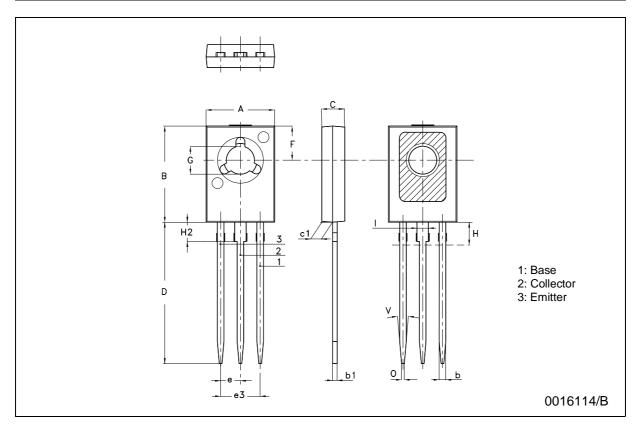
| Symbol | Parameter | Test Conditions | | Min. | Тур. | Max. | Unit |
|--------------------------------------|---|---|---|--|--------------------------|-------------------|----------------|
| Ісво | Collector Cut-off Current (I _E = 0) | for BD433/434 for BD435/436 for BD437/438 | $V_{CB} = 32 \text{ V}$ | | | 100 100 100 | μΑ μΑ μΑ |
| I _{CES} | Collector Cut-off Current (V _{BE} = 0) | for BD433/434 for BD435/436 for BD437/438 | $V_{CE} = 32 \text{ V}$ | | | 100 100 100 | μΑ μΑ μΑ |
| I _{EBO} | Emitter Cut-off Current (I _C = 0) | V _{EB} = 5 V | | | | 1 | mA |
| V _{CEO(sus)*} | Collector-Emitter Sustaining Voltage (I _B = 0) | I _C = 100 mA | for BD433/434 for BD435/436 for BD437/438 | 22 32 45 | | | V V V |
| VCE(sat)* | Collector-Emitter Saturation Voltage | I _C = 2 A | I _B = 0.2 A for BD433/434 for BD435/436 for BD437/438 | | 0.2 0.2 0.2 | 0.5 0.5 0.6 | V V V |
| V _{BE} * | Base-Emitter Voltage | I _C = 10 mA I _C = 2 A | $V_{CE} = 5 \text{ V}$ $V_{CE} = 1 \text{ V}$ for BD433/434 for BD435/436 for BD437/438 | | 0.58 | 1.1 1.1 1.2 | V V V |
| h _{FE} * | DC Current Gain | I _C = 10 mA I _C = 500 mA I _C = 2 A | V _{CE} = 5 V for BD433/434 for BD435/436 for BD437/438 V _{CE} = 1 V V _{CE} = 1 V for BD433/434 for BD435/436 | 40 40 30 85 50 50 40 | 130 130 130 140 | | |
| h _{FE1} /h _{FE2} * | Matched Pair | I _C = 500 mA | V _{CE} = 1 V | | | 1.4 | |
| f _T | Transition frequency | I _C = 250 mA | V _{CE} = 1 V | 3 | | | MHz |

^{*} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

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SOT-32 (TO-126) MECHANICAL DATA

| DIM. | | mm | | | inch | |
|------|------|------|------|-------|-------|-------|
| DIM. | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| Α | 7.4 | | 7.8 | 0.291 | | 0.307 |
| В | 10.5 | | 10.8 | 0.413 | | 0.425 |
| b | 0.7 | | 0.9 | 0.028 | | 0.035 |
| b1 | 0.40 | | 0.65 | 0.015 | | 0.025 |
| С | 2.4 | | 2.7 | 0.094 | | 0.106 |
| c1 | 1.0 | | 1.3 | 0.039 | | 0.051 |
| D | 15.4 | | 16.0 | 0.606 | | 0.630 |
| е | | 2.2 | | | 0.087 | |
| e3 | | 4.4 | | | 0.173 | |
| F | | 3.8 | | | 0.150 | |
| G | 3 | | 3.2 | 0.118 | | 0.126 |
| Н | | | 2.54 | | | 0.100 |
| H2 | | 2.15 | | | 0.084 | |
| 1 | | 1.27 | | | 0.05 | |
| 0 | | 0.3 | | | 0.011 | |
| V | | 10° | | | 10° | |



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